電漿輔助式原子層沉積系統

(PLASMA-ENHANCED ATOMIC LAYER DEPOSITION)

Deposition Process Library

- Hafnium Dioxide (HfO_2)
- Aluminum oxide (Al_2O_3)

Thickness

- 20A ~ 100Å

Process parameters

- Process: HfO_2
- Precursor: TEMAHf
- Pressure(torr): 0.5~1.5
- Carrier gas: Ar
- Purge gas: Ar
- Temperature (℃): 250 ℃
- Substrate size: 6, 8 inch, chip

- Process: Al_2O_3
- Precursor: TMA
- Pressure(mbar): 0.5~1.5
- Carrier gas: Ar
- Purge gas: Ar
- Temperature (℃): 250 ℃
- Substrate size: 6, 8 inch, chip